

FETs, IPD, IGBTs, GaAs MMICs

■ Silicon MOS FETs

● For Small Signal

Application	Struc- ture	Part No.	Absolute Maximum Ratings (T _a = 25 °C)				Electrical Characteristics (T _a = 25 °C)				Package		No.				
			V _{DS} *V _{DSS} (V)	V _{GSO} (V)	I _D (A)	P _D (mW)	Y _{fs} min. *typ. (mS)	R _{DS(on)} max. *typ. (Ω)	t _{on} max. *typ. (ns)	t _{off} max. *typ. (ns)							
Digital/ analog switching	N-ch	2SK0601 (2SK601)	80	20	0.5	1 000	*300	*2	*15	*20	MiniP3-F1	D34					
		2SK0614 (2SK614)				750					TO-92-A1	D56					
		2SK0615 (2SK615)				1 000					M-A1	D65					
		2SK0655 (2SK655)	50	8	0.1	200	20	50	10	20	NS-A1/NS-B1	D61/ D62					
		2SK0656 (2SK656)				400			1 000	1 000							
		2SK0657 (2SK657)							10	20	M-A1	D65					
		2SK0664 (2SK664)							40	1 000	1 000	SMini3-G1	D17				
		2SK0665 (2SK665)	20														
		2SK1228*	50	10	0.05	150	*39	*27	2 000	2 000	Mini3-G1	D26					
		2SK1374*		± 7	0.1						SMini3-G1	D17					
		2SK3539									SSMini3-F1	D8					
		Δ 2SK3546J			20		*8	*200	*200	SSSMini3-F1	D5						
		Δ 2SK3547	SSSMini3-F1			D5											
		2SK2211	30	± 20	1	1 000	500	*0.48	*12	*160	MiniP3-F1	D34					
		2SK3064	*30		0.1	150	15	30*	*150	*35	SMini3-G1	D17					
	P-ch	2SJ0536	*-30		- 0.1		8	50*	*100	*25							

Δ: Tentative *: 2.5 V Drive

Note) In the tables, part numbers show the Matsushita unified part numbers. And the part numbers in parentheses show the conventional ones.